

GESD8D36V

ESD Protection Diode

DESCRIPTION

The GESD8Z36V Series is designed to protect voltage sensitive components from ESD and transient voltage events. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in cellular phones, portable devices, digital cameras, power supplies and many other portable applications.

FEATURES

- ♦ Transient protection for high-speed data lines IEC 61000-4-2 (ESD) ±15kV (Air) ±8kV (Contact)
- ♦Protects one directional I/O or Vcc line
- Dow clamping voltageWorking voltages : 36V
- ♦Low leakage current

MACHANICAL DATA

- ♦DFN1006 package
- ♦Flammability Rating: UL 94V-0
- ♦ Packaging: Tape and Reel
- ♦ High temperature soldering guaranted: 260°C/10s
- ♦Reel size: 7 inch

ORDERING INFORMATION

Device: GESD8Z36VPackage: DFN1006

♦ Marking: YN

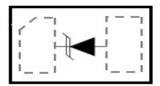
→ Material: Halogen free→ Packing: Tape & Reel

♦ Quantity per reel: 10,000pcs

APPLICATIONS

- ♦ Cell Phone Handsets and Accessories
- ♦ Microprocessor based equipment
- ♦ Personal Digital Assistants (PDA's)
- ♦Notebooks, Desktops, and Servers
- ♦ Portable Instrumentation
- ♦Peripherals
- ♦LED bypass

PIN CONFIGURATION



PACKAGE OUTLINE





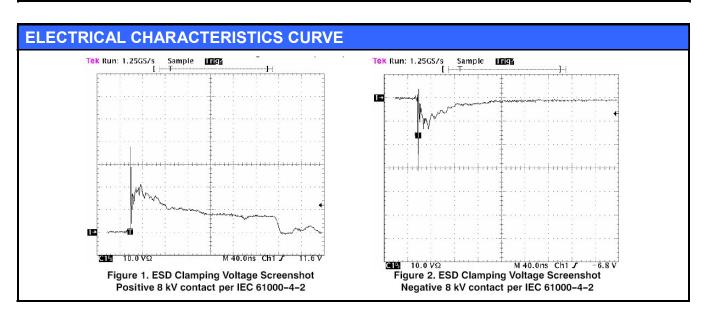
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ABSOLUTE MAXIMUM RATING						
Symbol	Parameter	Value	Units			
V _{ESD}	ESD per IEC 61000-4-2 (Air)	±25	kV			
	ESD per IEC 61000-4-2 (Contact)	±20				
P _D	Total Power Dissipation on FR-5 Board (Note 1) @ Ta=25°C	150	mW			
T _{OPT}	Operating Temperature	-55~125	°C			
T _{STG}	Storage Temperature	-55~150	°C			

These ratings are limiting values above which the serviceability of the diode may be impaired Note 1. FR-5=1.0x0.75x0.62 in.

ELECTRICAL CHARACTERISTICS (Tamb=25°C)								
Symbol	Parameter	Test Condition	Min	Тур	Max	Units		
V_{RWM}	Reverse Working Voltage				36	V		
V_{BR}	Reverse Breakdown Voltage	I _T = 1mA	40			V		
I _R	Reverse Leakage Current	V _{RWM} = 36V			5	μA		
V _C	Clamping Voltage	$I_{PP} = 1A, t_p = 8/20 \mu s$			55	V		
CJ	Junction Capacitance	V _R = 0V, f = 1MHz			28	pF		





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